Complementary Bias Resistor Transistors R1 = 22 k Ω , R2 = 22 k Ω

NPN and PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C both polarities Q₁ (PNP) & Q₂ (NPN), unless otherwise noted)

| | - · · · · | | |
|--------------------------------|----------------------|-----|------|
| Rating | Symbol | Max | Unit |
| Collector-Base Voltage | V _{CBO} | 50 | Vdc |
| Collector-Emitter Voltage | V _{CEO} | 50 | Vdc |
| Collector Current – Continuous | I _C | 100 | mAdc |
| Input Forward Voltage | V _{IN(fwd)} | 40 | Vdc |
| Input Reverse Voltage | V _{IN(rev)} | 10 | Vdc |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|---|---------|-----------------------|
| MUN5312DW1T1G, SMUN5312DW1T1G* | SOT-363 | 3,000 / Tape & Reel |
| NSVMUN5312DW1T3G* | SOT-363 | 10,000 / Tape & Reel |
| MUN5312DW1T2G, NSVMUN5312DW1T2G* | SOT-363 | 3,000 / Tape & Reel |
| NSBC124EPDXV6T1G, NSVBC124EPDXV6T1G* | SOT-563 | 4,000 / Tape & Reel |
| NSBC124EPDXV6T5G | SOT-563 | 8,000 / Tape & Reel |
| NSBC124EPDP6T5G | SOT-963 | 8,000 / Tape & Reel |

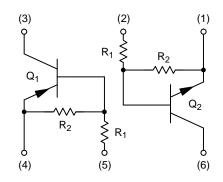
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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PIN CONNECTIONS



MARKING DIAGRAMS



SOT-363 CASE 419B-02





SOT-563 CASE 463A





SOT-963 CASE 527AD



12/R = Specific Device Code

M = Date Code*
■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

THERMAL CHARACTERISTICS

| | Characteristic | Symbol | Max | Unit |
|--|-------------------------------|-----------------------------------|--------------------------|-------------|
| MUN5312DW1 (SOT-363) ON | IE JUNCTION HEATED | • | | |
| Total Device Dissipation T _A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 2) | (Note 1) | P _D | 187 256 1.5 2.0 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{	heta JA}$ | 670 490 | °C/W |
| MUN5312DW1 (SOT-363) BC | OTH JUNCTION HEATED (Note 3) | | | |
| Total Device Dissipation $T_A = 25^{\circ}C \qquad (Note 1)$ $(Note 2)$ Derate above 25°C $(Note 2)$ | (Note 1) | P _D | 250 385 2.0 3.0 | mW mW/°C |
| Thermal Resistance, Junction to Ambient (Note 2) | (Note 1) | $R_{	hetaJA}$ | 493 325 | °C/W |
| Thermal Resistance, Junction to Lead (Note 1) (Note 2) | | $R_{	heta JL}$ | 188 208 | °C/W |
| Junction and Storage Temper | ature Range | T _J , T _{stg} | -55 to +150 | °C |
| NSBC124EPDXV6 (SOT-563) | ONE JUNCTION HEATED | | | |
| Total Device Dissipation T _A = 25°C (Note 1) Derate above 25°C | (Note 1) | P _D | 357 2.9 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) | $R_{	heta JA}$ | 350 | °C/W |
| NSBC124EPDXV6 (SOT-563) | BOTH JUNCTION HEATED (Note 3) | | | |
| Total Device Dissipation T _A = 25°C (Note 1) Derate above 25°C | (Note 1) | P _D | 500 4.0 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) | $R_{	heta JA}$ | 250 | °C/W |
| Junction and Storage Temper | ature Range | T _J , T _{stg} | -55 to +150 | °C |
| NSBC124EPDP6 (SOT-963) | ONE JUNCTION HEATED | | | |
| Total Device Dissipation $T_A = 25^{\circ}C$ (Note 4) (Note 5) Derate above 25°C (Note 5) | (Note 4) | P _D | 231 269 1.9 2.2 | MW mW/°C |
| Thermal Resistance, Junction to Ambient (Note 5) | (Note 4) | $R_{	hetaJA}$ | 540 464 | °C/W |
| NSBC124EPDP6 (SOT-963) | BOTH JUNCTION HEATED (Note 3) | | | |
| Total Device Dissipation T _A = 25°C (Note 4) (Note 5) Derate above 25°C (Note 5) | (Note 4) | P _D | 339 408 2.7 3.3 | MW mW/°C |
| Thermal Resistance, Junction to Ambient (Note 5) | (Note 4) | $R_{	hetaJA}$ | 369 306 | °C/W |
| Junction and Storage Temper | ature Range | T _J , T _{stg} | -55 to +150 | °C |

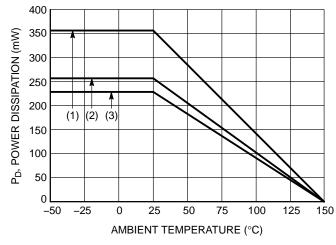
- 1. FR-4 @ Minimum Pad.
- FR-4 @ Millimum Pad.
 FR-4 @ 1.0 × 1.0 Inch Pad.
 Both junction heated values assume total power is sum of two equally powered channels.
 FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ both polarities Q_1 (PNP) & Q_2 (NPN), unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|--------------------------------|--------|------------|--------|------|
| OFF CHARACTERISTICS | <u> </u> | | | | |
| Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$ | Ісво | - | - | 100 | nAdc |
| Collector-Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$ | I _{CEO} | - | - | 500 | nAdc |
| Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0) | I _{EBO} | - | _ | 0.2 | mAdc |
| Collector-Base Breakdown Voltage (I _C = 10 μA, I _E = 0) | V _{(BR)CBO} | 50 | - | - | Vdc |
| Collector-Emitter Breakdown Voltage (Note 6) (I _C = 2.0 mA, I _B = 0) | V _{(BR)CEO} | 50 | - | _ | Vdc |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain (Note 6) (I _C = 5.0 mA, V _{CE} = 10 V) | h _{FE} | 60 | 100 | _ | |
| Collector-Emitter Saturation Voltage (Note 6) (I _C = 10 mA, I _B = 0.3 mA) | V _{CE(sat)} | _ | _ | 0.25 | V |
| Input Voltage (Off) $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}) \text{ (NPN)} $ $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}) \text{ (PNP)}$ | V _{i(off)} | - - | 1.2 1.2 | - - | Vdc |
| Input Voltage (On) $(V_{CE} = 0.2 \text{ V, } I_{C} = 5.0 \text{ mA}) \text{ (NPN)} $ $(V_{CE} = 0.2 \text{ V, } I_{C} = 5.0 \text{ mA}) \text{ (PNP)}$ | V _{i(on)} | - - | 1.9 2.0 | _ _ | Vdc |
| Output Voltage (On) ($V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$) | V _{OL} | - | _ | 0.2 | Vdc |
| Output Voltage (Off) ($V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$) | V _{OH} | 4.9 | _ | _ | Vdc |
| Input Resistor | R1 | 15.4 | 22 | 28.6 | kΩ |
| Resistor Ratio | R ₁ /R ₂ | 0.8 | 1.0 | 1.2 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.



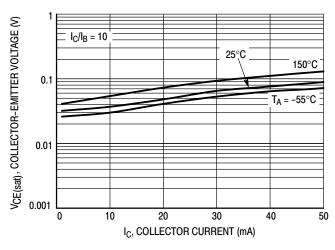
(1) SOT-363; 1.0×1.0 Inch Pad

Figure 1. Derating Curve

⁽²⁾ SOT-563; Minimum Pad

⁽³⁾ SOT-963; 100 mm², 1 oz. Copper Trace

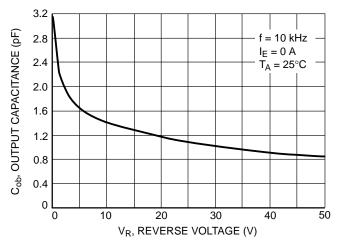
TYPICAL CHARACTERISTICS – NPN TRANSISTOR MUN5312DW1, NSBC124EPDXV6



1000 V_{CE} = 10 V T_A = 150°C T_A = 150°C

Figure 2. V_{CE(sat)} vs. I_C

Figure 3. DC Current Gain



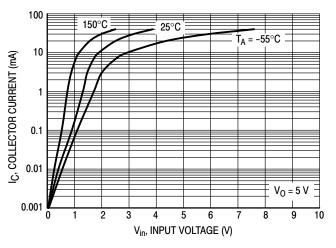


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

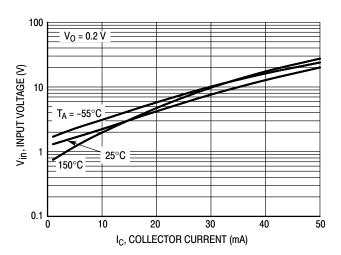


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – PNP TRANSISTOR MUN5312DW1, NSBC124EPDXV6

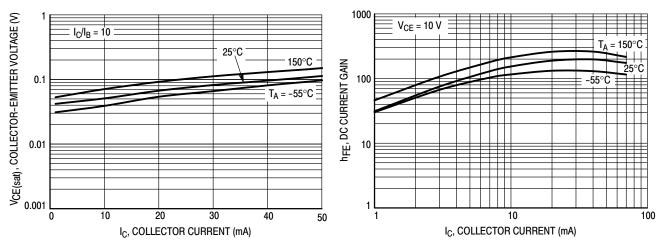


Figure 7. V_{CE(sat)} vs. I_C

Figure 8. DC Current Gain

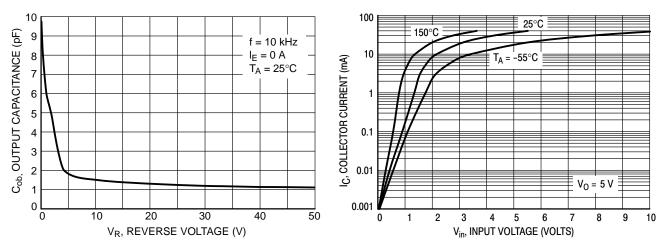


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

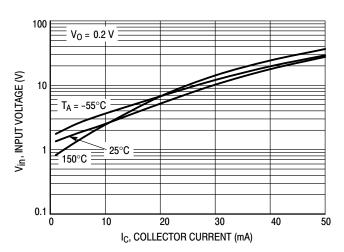


Figure 11. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – NPN TRANSISTOR NSBC124EPDP6

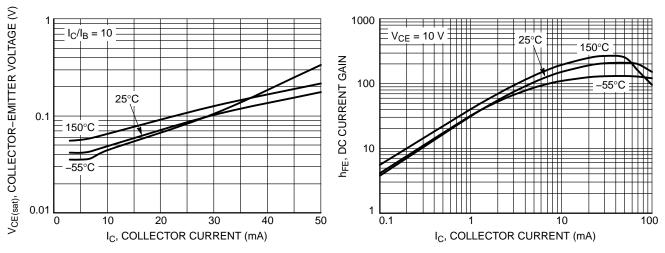


Figure 12. V_{CE(sat)} vs. I_C

Figure 13. DC Current Gain

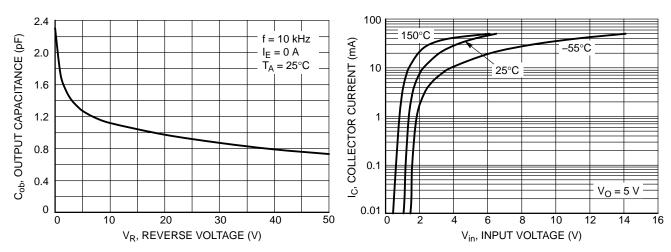


Figure 14. Output Capacitance

Figure 15. Output Current vs. Input Voltage

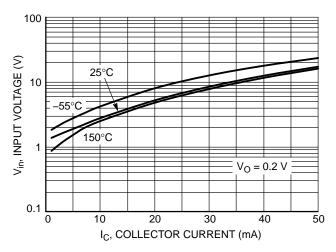


Figure 16. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – PNP TRANSISTOR NSBC124EPDP6

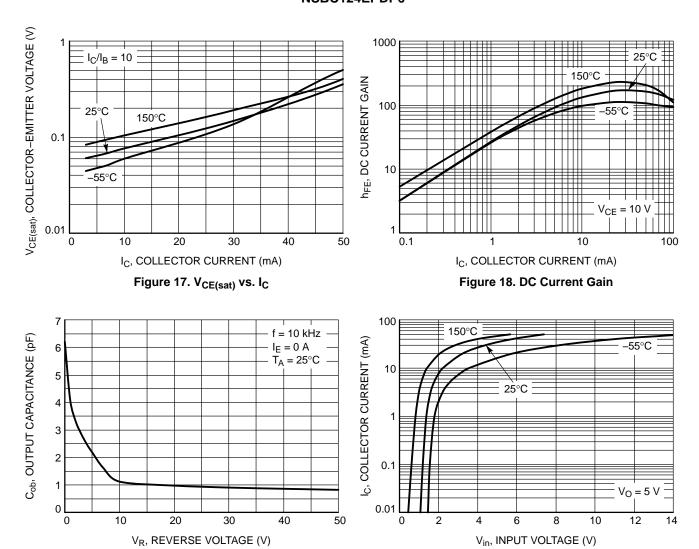


Figure 19. Output Capacitance

Figure 20. Output Current vs. Input Voltage

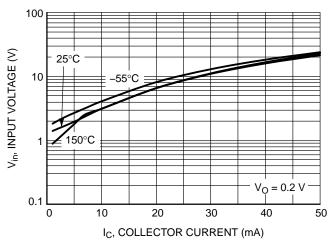


Figure 21. Input Voltage vs. Output Current





E1

6X 0.30 -

e

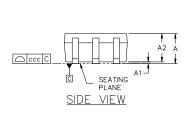
В

SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

DATE 18 APR 2024

NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
- DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 DATUMS A AND B ARE DETERMINED AT DATUM H.
- DIMENSIONS 6 AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.



TOP VIEW

∆aaa H A−B

<u></u> БЬБ С

⊕ ddd M C A−B D

6X 0.66

2.50





| | MILLIMETERS | | | |
|-----|-------------|----------|------|--|
| DIM | MIN. | NOM. | MAX. | |
| Α | | | 1.10 | |
| A1 | 0.00 | | 0.10 | |
| A2 | 0.70 | 0.90 | 1.00 | |
| b | 0.15 | 0.20 | 0.25 | |
| С | 0.08 | 0.15 | 0.22 | |
| D | 2.00 BSC | | | |
| E | 2.10 BSC | | | |
| E1 | 1.25 BSC | | | |
| е | | 0.65 BSC | ; | |
| L | 0.26 | 0.36 | 0.46 | |
| L2 | 0.15 BSC | | | |
| aaa | 0.15 | | | |
| bbb | 0.30 | | | |
| ccc | 0.10 | | | |
| ddd | 0.10 | | | |

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

- *Date Code orientation and/or position may vary depending upon manufacturing location.
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLES ON PAGE 2

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| DESCRIPTION: | SC-88 2.00x1.25x0.90, 0.65 | 5P | PAGE 1 OF 2 |

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SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

| STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2 | STYLE 2: CANCELLED | STYLE 3: CANCELLED | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2 |
|--|--|---|---|---|--|
| STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2 | STYLE 8: CANCELLED | STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2 | STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2 | STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2 | STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2 |
| STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC | STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1 | STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1 | STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1 | STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1 |
| STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF | STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR | STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1 | STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c) | STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C | STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE |
| STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1 | STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1 | STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2 | STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN | STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE | STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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|------------------|-----------------------------|---|-------------|
| DESCRIPTION: | SC-88 2.00x1.25x0.90, 0.65P | | PAGE 2 OF 2 |

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STYLE 4:

STYLE 10:

PIN 1. CATHODE 1

2. N/C 3. CATHODE 2

4. ANDDE 2

PIN 1. COLLECTOR 2. COLLECTOR

3. BASE

4. EMITTER
5. COLLECTOR
6. COLLECTOR

SOT-563-6 1.60x1.20x0.55, 0.50P CASE 463A **ISSUE J**

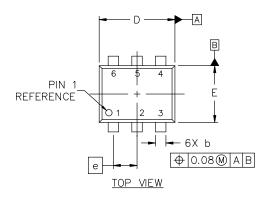
DATE 15 FEB 2024

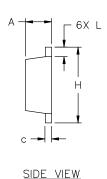
NOTES:

- 1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

DIM

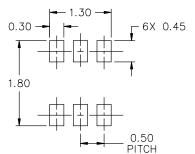
MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.





| MIG | MIN. | N□M. | MAX. |
|-----|----------|------|------|
| А | 0.50 | 0.55 | 0.60 |
| b | 0.17 | 0.22 | 0.27 |
| С | 0.08 | 0.13 | 0.18 |
| D | 1.50 | 1.60 | 1.70 |
| E | 1.10 | 1.20 | 1.30 |
| е | 0.50 BSC | | |
| Н | 1.50 | 1.60 | 1.70 |
| L | 0.10 | 0.20 | 0.30 |

MILLIMETERS



| STYLE 1 | STVI F. O. | STYLE O |
|------------------|------------------|------------------|
| STYLE 1: | STYLE 2: | STYLE 3: |
| PIN 1. EMITTER 1 | PIN 1. EMITTER 1 | PIN 1. CATHODE 1 |
| 2. BASE 1 | 2. EMITTER 2 | 2. CATHODE 1 |
| 3. COLLECTOR 2 | 3. BASE 2 | 3. ANODE/ANODE 2 |
| 4. EMITTER 2 | 4. COLLECTOR 2 | 4. CATHODE 2 |
| 5. BASE 2 | 5. BASE 1 | 5. CATHODE 2 |
| 6. COLLECTOR 1 | 6. COLLECTOR 1 | 6. ANODE/ANODE 1 |
| | | |
| | | |

STYLE 6: PIN 1. CATHODE 2. ANODE

CATHODE

CATHODE

4. CATHODE 5. CATHODE

| RECOMMENDED | MOUNTING | FOOTPRINT* |
|-------------|----------|------------|

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

| STYLE 7: | STYLE 8: | STYLE 9: |
|----------------|--------------|-----------------|
| PIN 1. CATHODE | PIN 1. DRAIN | PIN 1. SOURCE 1 |
| 2. ANODE | 2. DRAIN | 2. GATE 1 |
| 3. CATHODE | 3. GATE | 3. DRAIN 2 |
| 4. CATHODE | 4. SOURCE | 4. SOURCE 2 |
| 5. AN□DE | 5. DRAIN | 5. GATE 2 |
| 6. CATHODE | 6. DRAIN | 6. DRAIN 1 |
| | | |

PIN 1. EMITTER 2

2. BASE 2 3. COLLECTOR 1

4. EMITTER 1

STYLE 11:

STYLE 5:

3. ANDDE

PIN 1. CATHODE 2. CATHODE

4. ANDDE 5. CATHODE

6. CATHODE

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Month Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| DESCRIPTION: | SOT-563-6 1.60x1.20x0.55 | 5, 0.50P | PAGE 1 OF 1 | |
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| | 5. BASE 1 6. COLLECTOR 2 | or may not be present. Some products may not follow the Generic Marking. | | |

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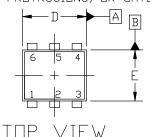


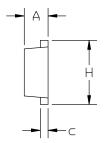
SOT-963 1.00x1.00x0.37, 0.35P CASE 527AD ISSUE F

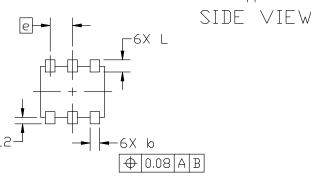
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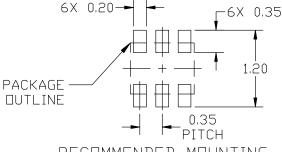
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.







MILLIMETERS DIM MIN. $N\square M$. MAX. 0.37 0.40 Α 0.34 0.10 0.15 0.20 h \subset 0.07 0.12 0.17 D 0.95 1.00 1.05 Ε 0.75 0.80 0.85 0.35 BSC 6 Н 1.00 0.95 1.05 0.19 REF L2 0.05 0.10 0.15



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference manual, SDLDERRM/D.

BOTTOM VIEW

| STYLE 1: PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 | STYLE 2: PIN 1. EMITTER 1 2. EMITTER2 3. BASE 2 4. COLLECTOR 2 | STYLE 3: PIN 1. CATHODE 1 2. CATHODE 1 3. ANODE/ANODE 2 4. CATHODE 2 |
|---|--|--|
| 5. BASE 2 6. COLLECTOR 1 | 5. BASE 1 6. COLLECTOR 1 | CATHODE 2 ANODE/ANODE 1 |
| STYLE 4: | STYLE 5: | STYLE 6: |

STYLE 4: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE
STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2

4. ANODE 2

6. ANODE 1

5. N/C

STYLE 5: PIN 1. CATHODE 2. CATHODE 3. ANODE 4. ANODE 5. CATHODE

5. CATHODE 5
6. CATHODE 6
STYLE 8: STYLE
PIN 1. DRAIN PIN 1
2. DRAIN 2
3. GATE 3
4. SOURCE 4
5. DRAIN 5
6. DRAIN 6

STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE

STYLE 9: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1 GENERIC
MARKING DIAGRAM*



XX = Specific Device CodeM = Month Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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| DESCRIPTION: | SOT-963 1.00x1.00x0.37, 0.35P | | PAGE 1 OF 1 | |

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